/ Descriptions

TO-126F NPN Silicon NPN transistor in a TO-126F Plastic Package.

/ Features

KSE350

High collector-Emitter breakdown voltage Suitable for transformer complement to KSE350.

/ Applications

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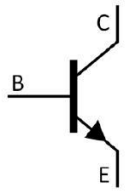
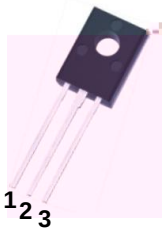
High voltage general purpose applications.

/ Equivalent Circuit



/ Pinning



PIN1 Emitter PIN 2 Collector PIN 3 Base

/ h_{FE} Classifications & Marking

See Marking Instructions.

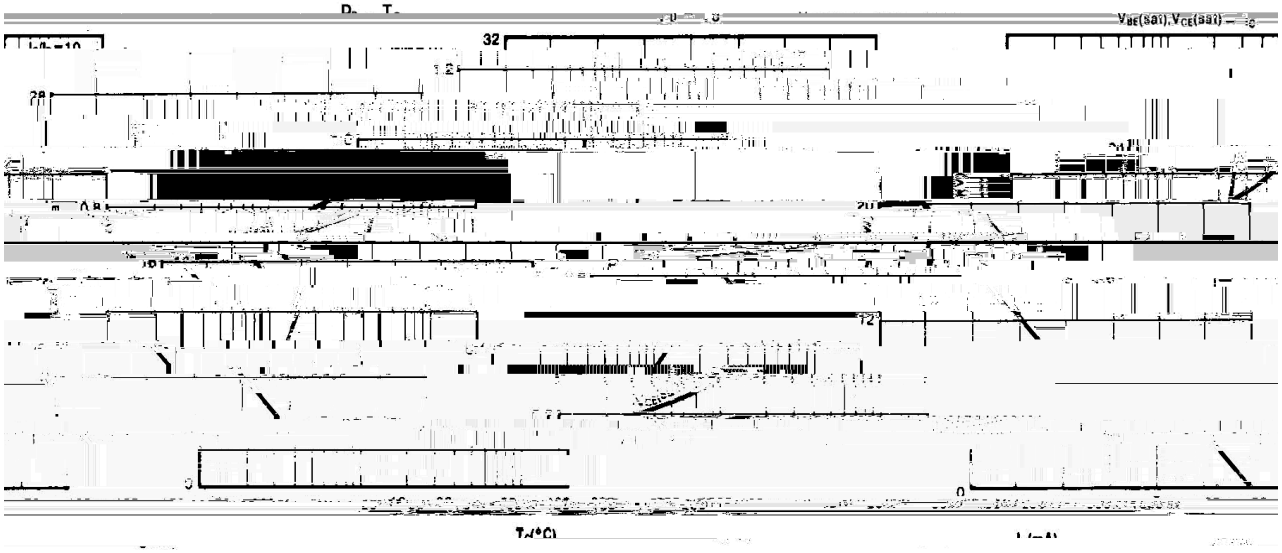
/ Absolute Maximum Ratings(Ta=25)

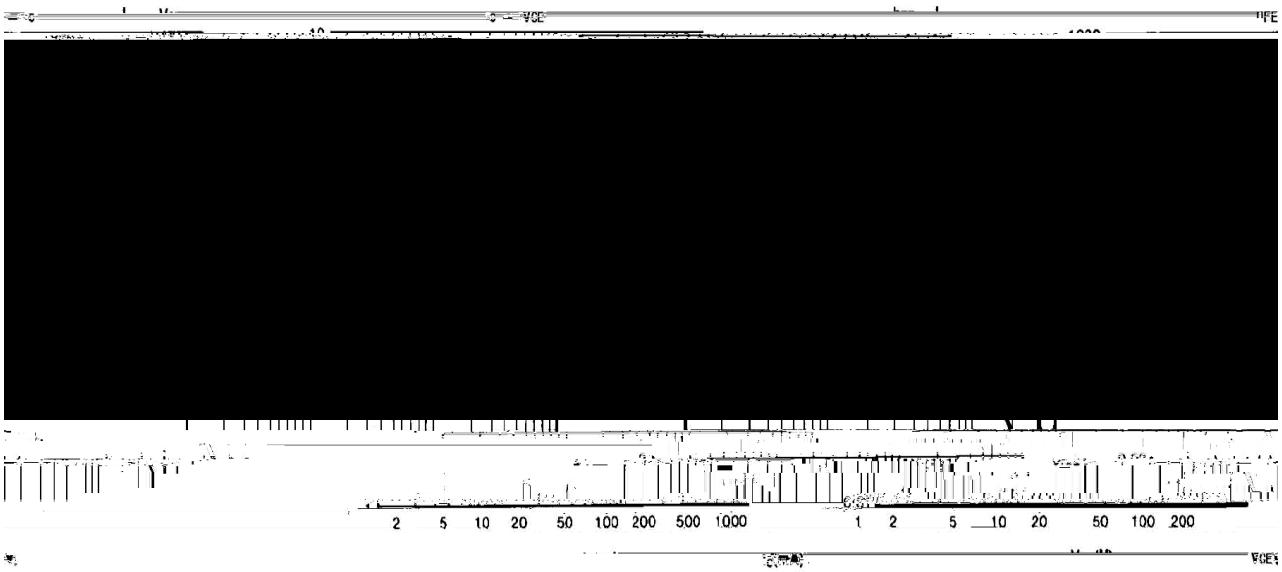
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	300	V
Collector to Emitter Voltage	V_{CEO}	300	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current – Continuous	I_C	500	mA
Collector Power Dissipation	$P_{C(Tc=25\ )}$	20	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

/ Electrical Characteristics(Ta=25)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Base Breakdown Voltage	V_{CBO}	I_C=0.1mA I_E=0	300			V
Collector to Emitter Breakdown Voltage	V_{CEO}	I_C=1.0mA I_B=0	300			V
Emitter to Base Breakdown Voltage	V_{EBO}	I_E=0.1mA I_C=0	5.0			V
Collector Cut-Off Current	I_{CBO}	V_{CB}=300V I_E=0			100	μA
Emitter Cut-off Current	I_{EBO}	V_{BE}=3.0V I_C=0			100	μA
DC Current Gain	h_{FE}	V_{CE}=10V I_C=50mA	30		240	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=50mA I_B=5mA			1.0	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=50mA I_B=5mA			1.2	V

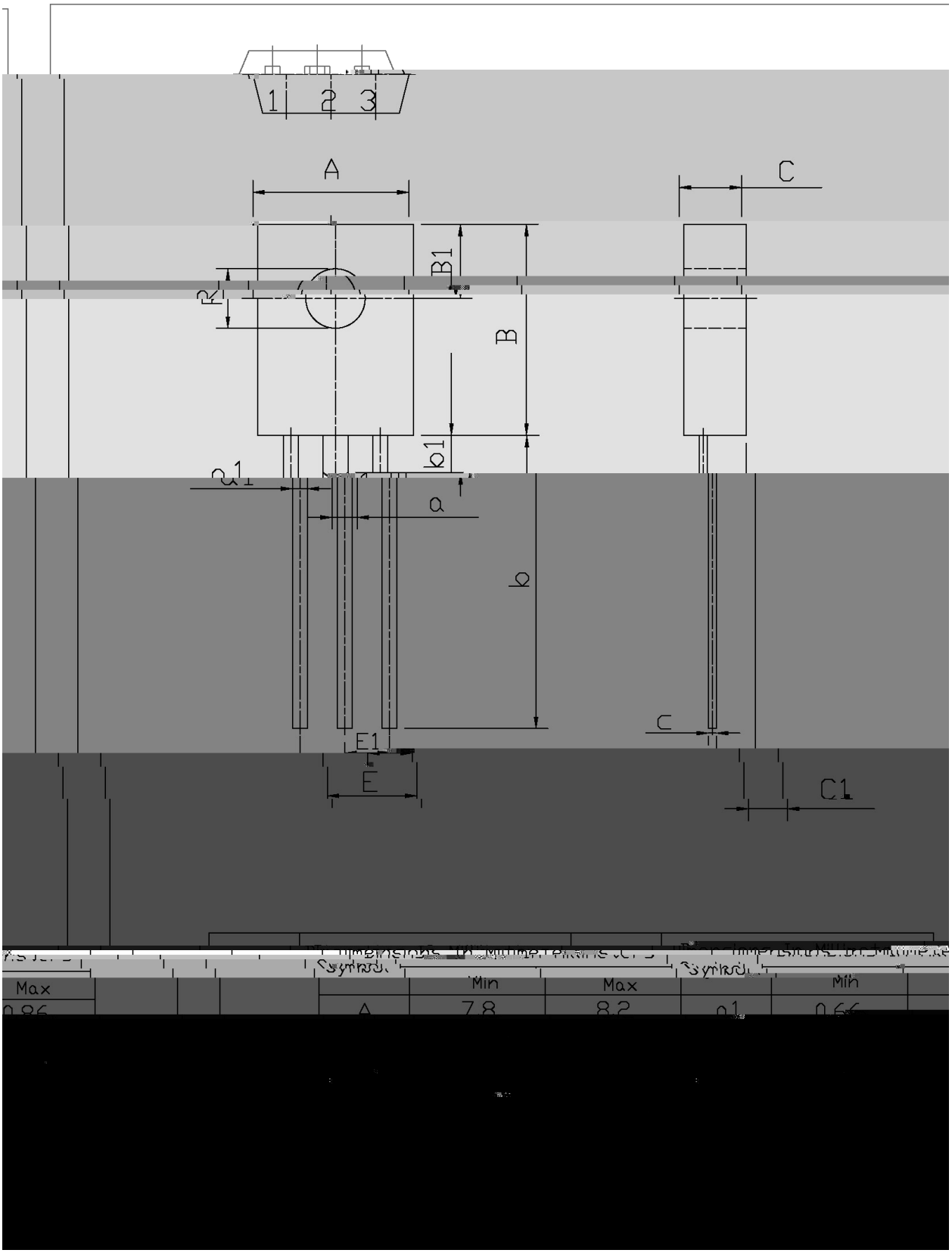
/ Electrical Characteristic Curve





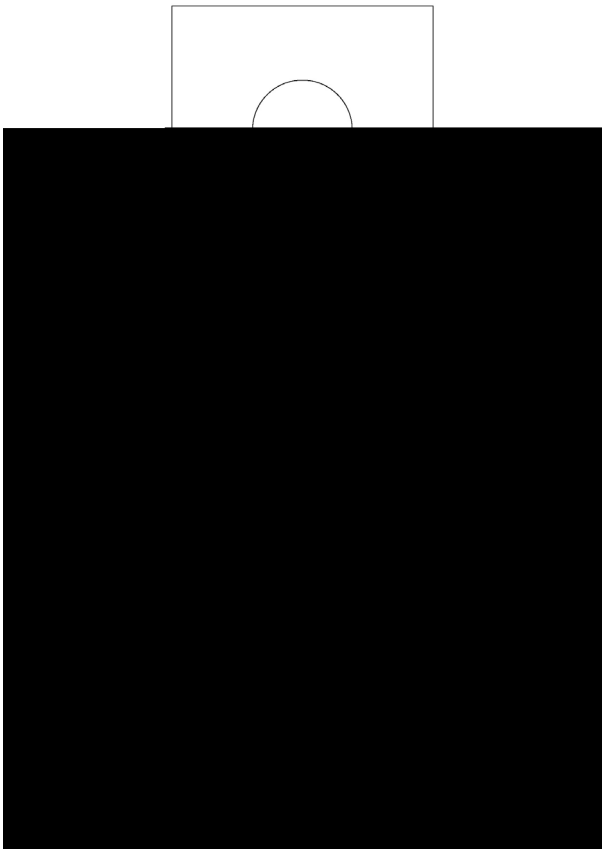
/ Package Dimensions

单位：mm



Symbol	Min	Max	Symbol	Min
A	7.8	8.2	a1	0.66

/ Marking Instructions



BR

KSE340

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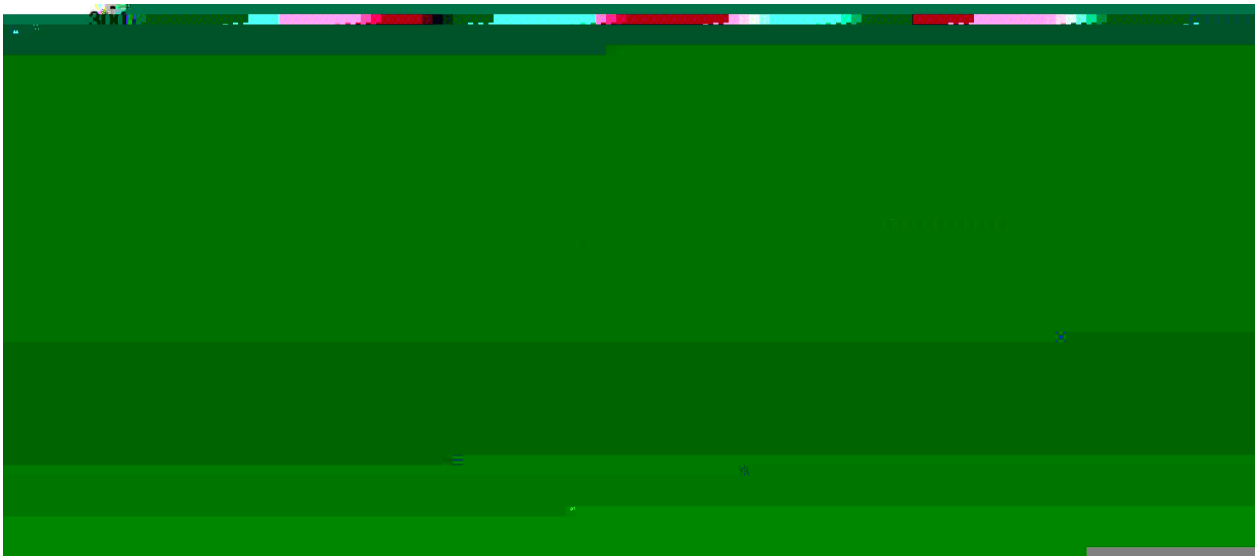
Note:

BR:	Company Code
KSE340:	Product Type.
****:	Lot No. Code, code change with Lot No.

( ) / Temperature Profile for Dip Soldering(Pb-Free)



Note: